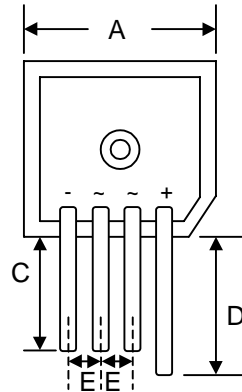


Features

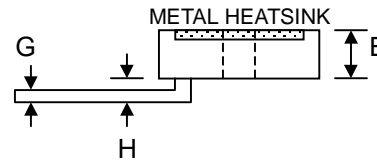
- Glass Passivated Die Construction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- Designed for Saving Mounting Space
- UL Recognized File # E157705

Mechanical Data

- Case: Epoxy Case with Heat Sink Internally Mounted in the Bridge Encapsulation
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Weight: 30 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



KBPC-S		
Dim	Min	Max
A	28.40	28.70
B	10.97	11.23
C	13.90	—
D	19.10	—
E	5.10	—
G	1.20 Ø Typical	
H	3.05	3.60
All Dimensions in mm		



Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristics	Symbol	-00S	-01S	-02S	-04S	-06S	-08S	-10S	Unit
Peak Repetitive Reverse Voltage	V_{RRM}								V
Working Peak Reverse Voltage	V_{RWM}	50	100	200	400	600	800	1000	
DC Blocking Voltage	V_R								
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Average Rectified Output Current @ $T_C = 55^\circ\text{C}$	I_O				40	50			A
Non-Repetitive Peak Forward Surge Current, 8.3ms Single Half-sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}				400	400			A
Forward Voltage Drop (per element)	V_{FM}				1.1				V
Peak Reverse Current at Rated DC Blocking Voltage (per element)	I_R				5.0	500			μA
Typical Thermal Resistance (per element) (Note 1)	$R_{\theta JC}$				1.5				K/W
RMS Isolation Voltage from Case to Lead	V_{ISO}				2500				V
Operating and Storage Temperature Range	T_j, T_{STG}				-65 to +150				$^\circ\text{C}$

Note: 1. Thermal resistance junction to case per element mounted on 220 x 220 x 50mm thick AL plate.

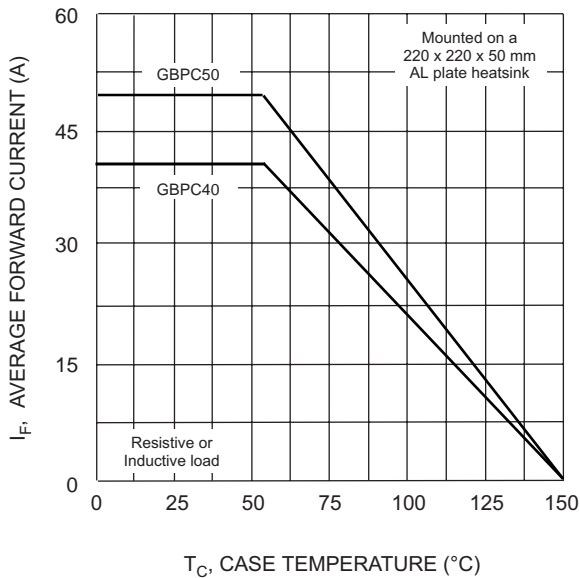


Fig. 1 Forward Current Derating Curve

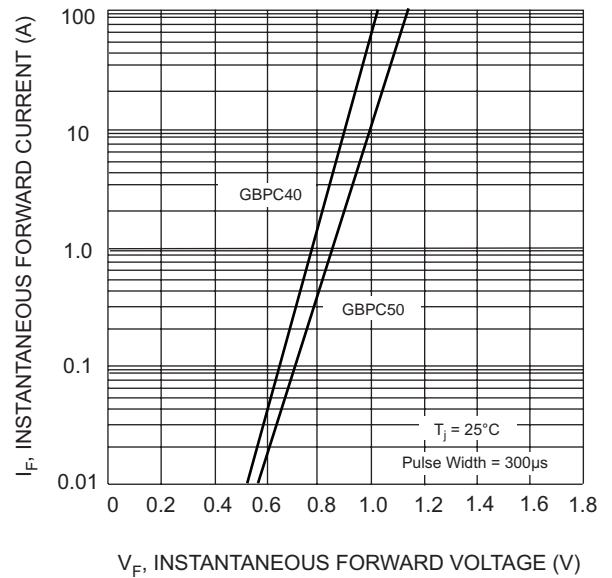


Fig. 2 Typical Forward Characteristics (per element)

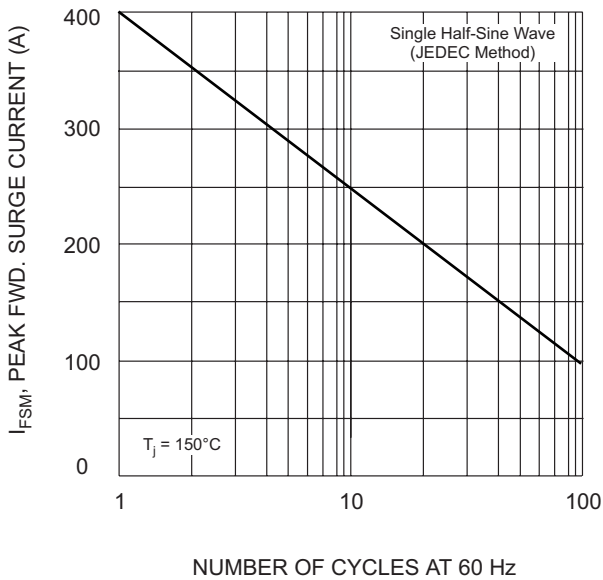


Fig. 3 Max Non-Repetitive Surge Current

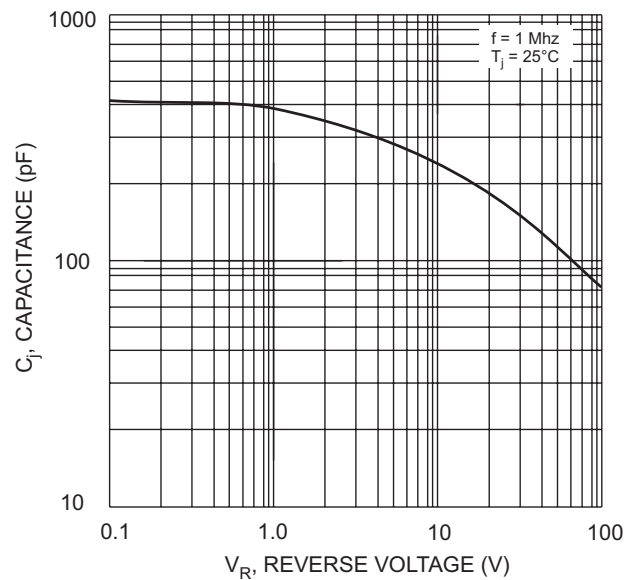


Fig. 4 Typical Junction Capacitance (per element)

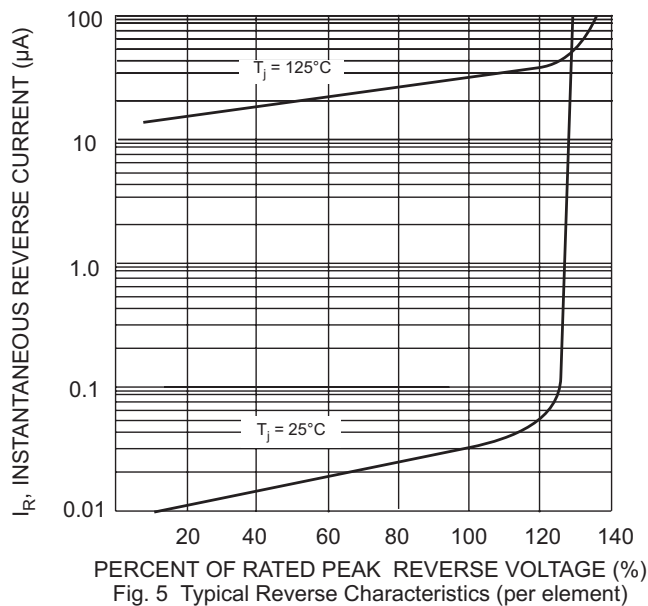


Fig. 5 Typical Reverse Characteristics (per element)

ORDERING INFORMATION

Product No.	Package Type	Shipping Quantity
GBPCxx00S	SIL Bridge	72 Units/Box
GBPCxx01S	SIL Bridge	72 Units/Box
GBPCxx02S	SIL Bridge	72 Units/Box
GBPCxx04S	SIL Bridge	72 Units/Box
GBPCxx06S	SIL Bridge	72 Units/Box
GBPCxx08S	SIL Bridge	72 Units/Box
GBPCxx10S	SIL Bridge	72 Units/Box

Shipping quantity given is for minimum packing quantity only. For minimum order quantity, please consult the Sales Department.

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Won-Top Electronics Co., Ltd.

No. 44 Yu Kang North 3rd Road, Chine Chen Dist., Kaohsiung, Taiwan

Phone: 886-7-822-5408 or 886-7-822-5410

Fax: 886-7-822-5417

Email: sales@wontop.com

Internet: <http://www.wontop.com>

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